

In the Claims:

Amend claims 1 and 53 as follows:

1. (Amended) A method comprising the step of annealing at least one region of a semiconductor substrate while minimizing the diffusion of dopant atoms during activation by using a pulsed beam of particles having a time duration less than or equal to 10^{-4} seconds.

53. (Amended) A method comprising the steps of annealing at least one integrated device formed in a semiconductor substrate while minimizing the diffusion of dopant atoms during activation by using a pulsed beam of particles having a duration between 10^{-10} seconds and 10^{-4} seconds.

REMARKS

Claims 1, 7, 14, 16-20, 22-23, 53, 61, 63-66, 69 and 71-72 were again rejected by the Examiner as being obvious from Asakawa (JP 06340500). Of those claims, claims 1 and 53 are independent claims and will be addressed first.

As amended, Claim 1 calls for "annealing at least one region of a semiconductor substrate while minimizing the diffusion of dopant atoms during activation by using a pulsed beam of particles having a time duration less than or equal to 10^{-4} seconds".

As amended, Claim 53 calls for "annealing at least one integrated device formed in a semiconductor substrate while minimizing the diffusion of dopant atoms during activation by using a pulsed beam of particles having a duration between 10^{-10} seconds and 10^{-4} seconds."

It can be seen that the method of both of Claims 1 and 53 is applied to a